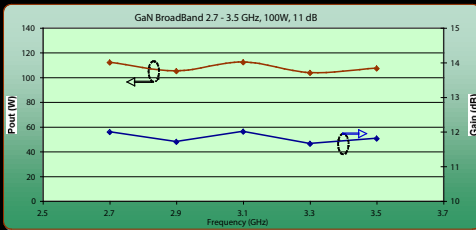


RF Power Transistors

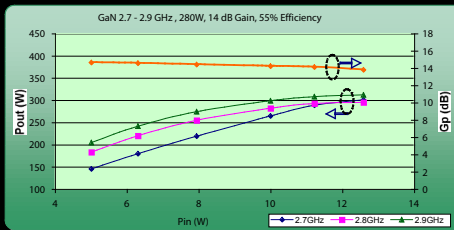
GaN S-Band Power for Maximum Performance



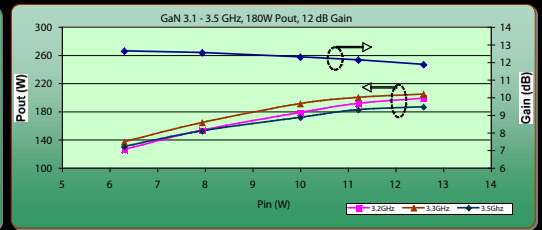
Broadband 2.7 - 3.5GHz



Power/Efficiency - 280W, +55%

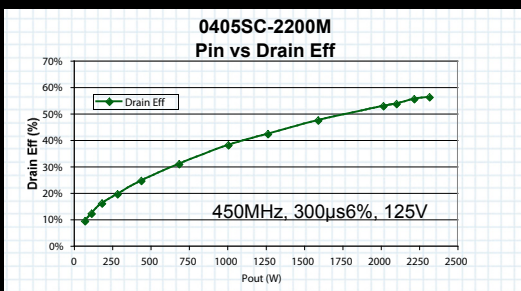
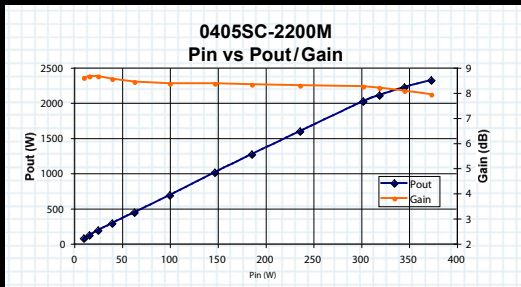


Power/Gain to 3.5GHz



- Small and Compact
- Extra Broad Band
- Exceptional Power
- Superior Gain Performance
- Excellent Drain Efficiency
- Outstanding Long Term Reliability

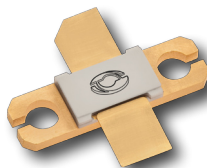
Silicon Carbide UHF SIT For Highest Peak Power



- Class AB
- 300µs Pulse Width
- 125V Bias
- 10:1 VSWR
- All gold Metallization
- Rad Tolerant



GaN S-Band Power for Maximum Performance



Frequency	2.7 - 3.5 GHz		2.7 - 2.9 GHz		2.7 - 3.1 GHz		3.1 - 3.5 GHz	
Pulse Format	300 us, 10%		100 us, 10%		200 us, 10%		300 us, 10%	
Model No.	2735GN-100	2735GN-30	2729GN-270	2729GN-150	2731GN-200	2731GN-110	3135GN-170	3135GN-100
Power (typ)	100 W	30 W	280 W	160 W	220 W	120 W	180 W	115 W
Power Gain (typ)	11 dB	11 dB	13 ~ 14dB	13 ~ 14dB	12 ~ 13 dB	12 ~ 13 dB	11~ 12 dB	11~ 12 dB

Silicon Carbide UHF SIT For Highest Peak Power



0150SC-1250M 0405SC-100M 0405SC-500M 0405SC-1000M 0405SC-1500M 0405SC-2200M

Band	VHF	UHF	UHF	UHF	UHF	UHF
Freq:	150 MHz	406-450 MHz	406-450 MHz	406-450 MHz	406-450 MHz	406-450 MHz
Power Out:	1250 W	100 W	500 W	1000 W	1500 W	2200 W
Power Gain:	9.5 dB	10 dB	10 dB	8.5 dB	8 dB	8 dB
Pulse Width:	300 μs	300 μs	300 μs	300 μs	300 μs	300 μs
Duty Cycle:	10%	10%	10%	10%	6%	6%
VSWR-T:	10:1	10:1	10:1	10:1	10:1	10:1
Efficiency:	60%	50%	50%	55%	55%	55%
Bias:	125V	125V	125V	125V	125V	125V
Case:	ST-FET	KT-FET	KT-FET	ST-FET	ST-FET	TW-FET
Metallization:	all AU	all AU	all AU	all AU	all AU	all AU
Rad Tolerant:	Yes	Yes	Yes	Yes	Yes	Yes

